Supporting Information:

UV-Vis-NIR Broadband Dual-Mode Photodetector Based on Graphene/InP Van der Waals Heterostructure

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Supplementary Figures:

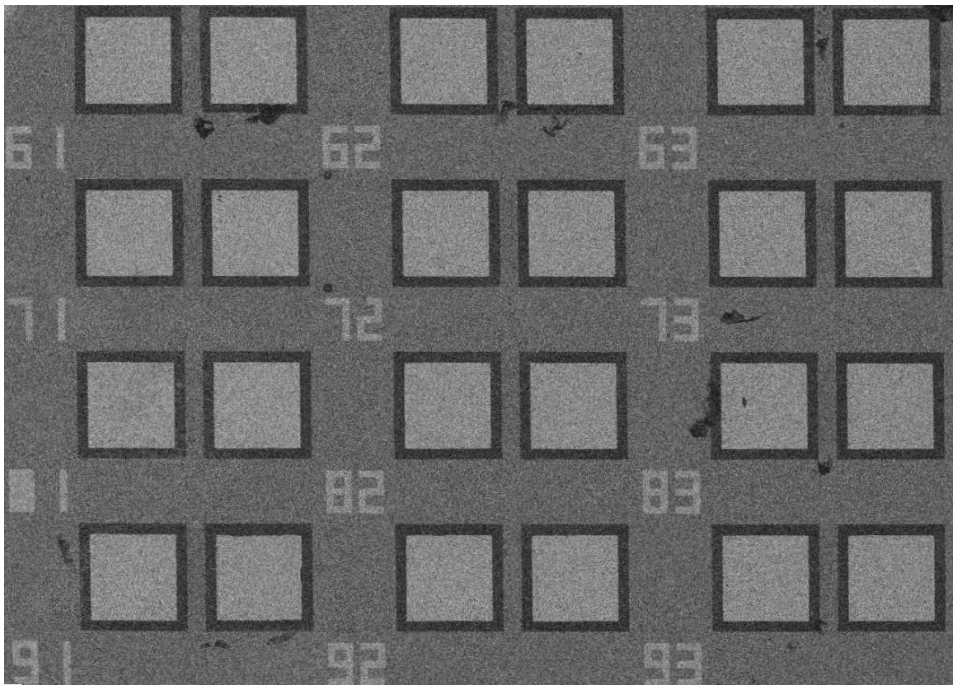


Figure S1. SEM image of 4×3 array of the graphene/InP van der Waals heterostructure DmPDs.

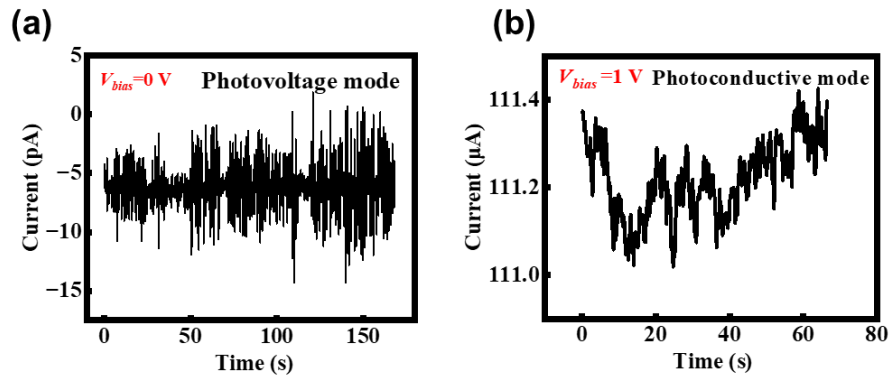


Figure S2. (a) Dark *I-T* curves of graphene/InP van der Waals heterostructure DmPDs working in the photovoltaic mode at zero bias and (b) in photoconductive mode at 1 V bias.

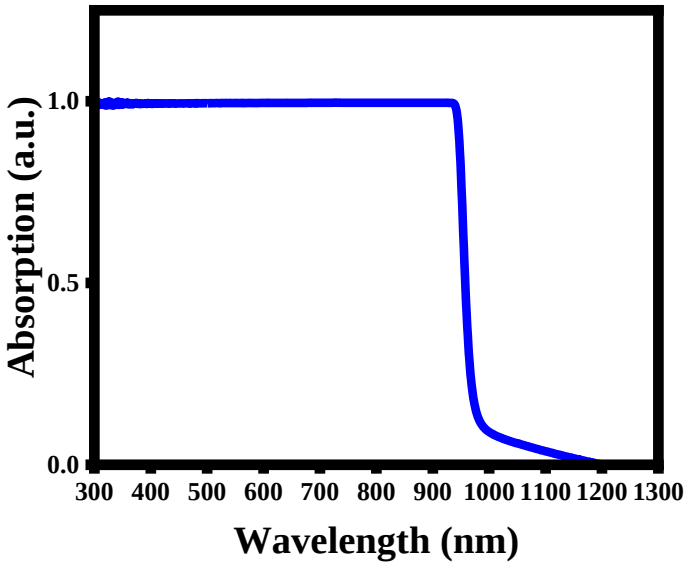


Figure S3. Absorption spectrum of InP ranging from 300 to 1200 nm.